VCR3P

P-Channel Silicon Voltage Controlled Resistor JFET

- Small Signal Attenuators
- Filters
- Amplifier Gain Control
- Oscillator Amplitude Control

Absolute maximum ratings at T_A = 5°C.

Reverse Gate Source & Reverse Gate Drain Voltage	15 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	300 mW
Power Derating	2.4 mW/°C

At 25°C free air temperature: Static Electrical Characteristics		VCR3P Min	VCR3P Max	Process PJ99 Unit	Process PJ99 Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	15		V	I_G = 1 µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		20	nA	V_{GS} = 15V, V_{DS} = ØV	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	1	5	V	I_D = – 1 µA, V_{DS} = – 10V	
Dynamic Electrical Characteristics						
Drain Source ON Resistance	$r_{ds(on)}$	70	200	Ω	V_{GS} = ØV, I_D = ØA	f = 1 kHz
Drain Gate Capacitance	C_{dg}		25	pF	V_{DG} = 10V, I_S = ØA	f = 1 MHz
Source Gate Capacitance	C_{sg}		15	pF	V_{GS} = 10V, I_D = ØA	f = 1 MHz

TO-18 Package
Dimensions in Inches (mm)

Pin Configuration
1 Source, 2 Gate & Case, 3 Drain

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